

1. Scope

The present specifications shall apply to an SJPZ-E33.

2. Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	Over Voltage Absorption

3. Flammability

UL94V-0 (Equivalent)

Not Recommended for New Designs

4. Absolute maximum ratings

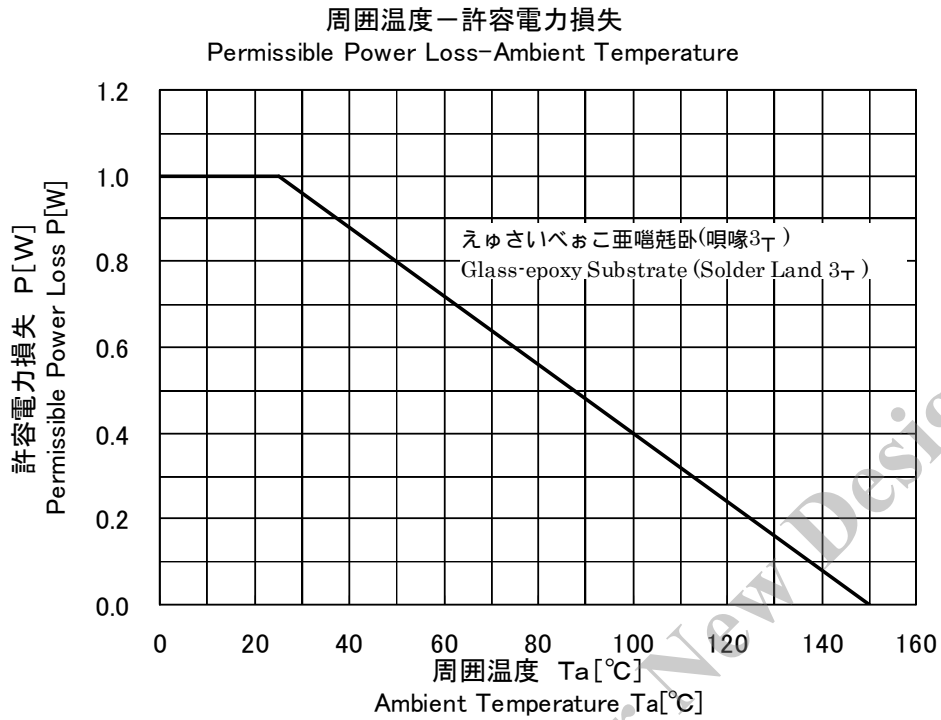
No.	Item	Symbol	Unit	Rating	Conditions
1	Permissible Power loss	P	W	1	Refer to Derating of 6
2	Transient Peak Reverse Power	P_{RSM}	W	95	Single Square Wave
3	Junction Temperature	T_j	°C	-55~+150	—
4	Storage Temperature	T_{stg}	°C	-55~+150	—

5. Electrical characteristics($T_a=25^{\circ}\text{C}$ (e)unless otherwise specified)

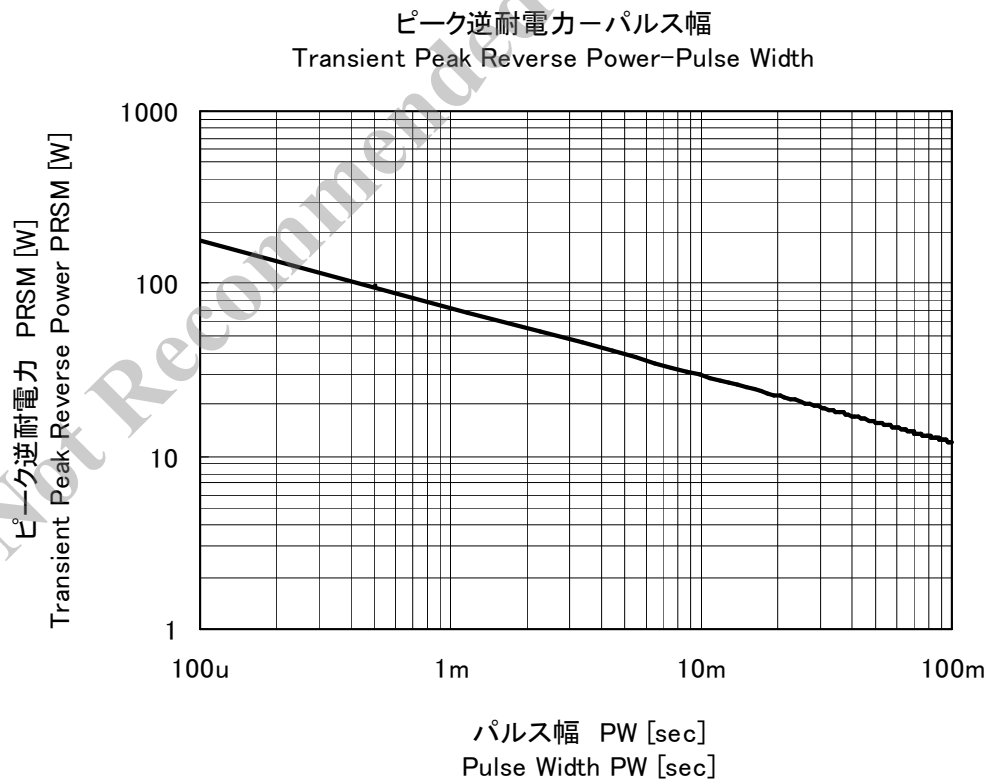
No.	Item	Symbol	Unit	Value	Conditions
1	Reverse Breakdown Voltage	V_Z	V	31.0 $\text{\textcircled{D}}$ 35.0	$I_Z=1\text{mA}$
2	Reverse Leakage Current	I_R	μA	10 max.	$V_R=25\text{V}$
3	Temperature Coefficient Breakdown Voltage	γ_z	$\text{mV}/^{\circ}\text{C}$	28 typ.	$\varphi I_Z=1\text{mA}$
4	Equivalent Resistance of Breakdown Region	R_z	Ω	10 typ.	$\varphi I_Z=10\text{mA}\text{\textcircled{D}}20\text{mA}$

6. Derating

Permissible Power Loss

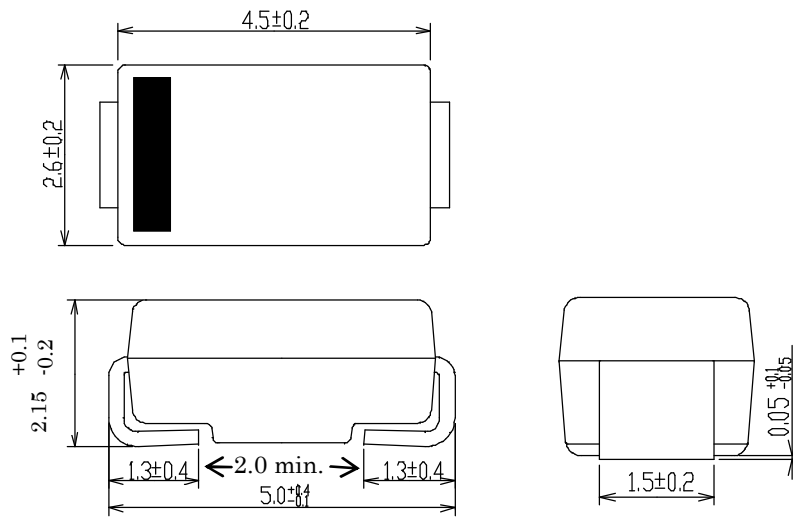


7. Transient Peak Reverse Power Rating



8. Package information

8-1 Package type, physical dimensions

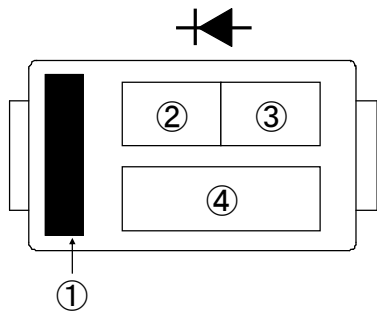


Dimensions in 眩

8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking



的 Polarity marking (Cathode band)

𠄎 Type number
SJPZ-E as abbreviated of ZE.

𠄎 Vz Class number
33V as abbreviated of 33.

𠄎 Lot number
Example) 6508
6: Last number of Year
5: Month from 1 to 9 for Jan. to Sep. O for Oct. (e)N for Nov. (e)D for Dec.
08: Day.

Not Recommended for New Designs